

SCHOTTKY BARRIER DIODE AND MANUFACTURING METHOD THEREFOR

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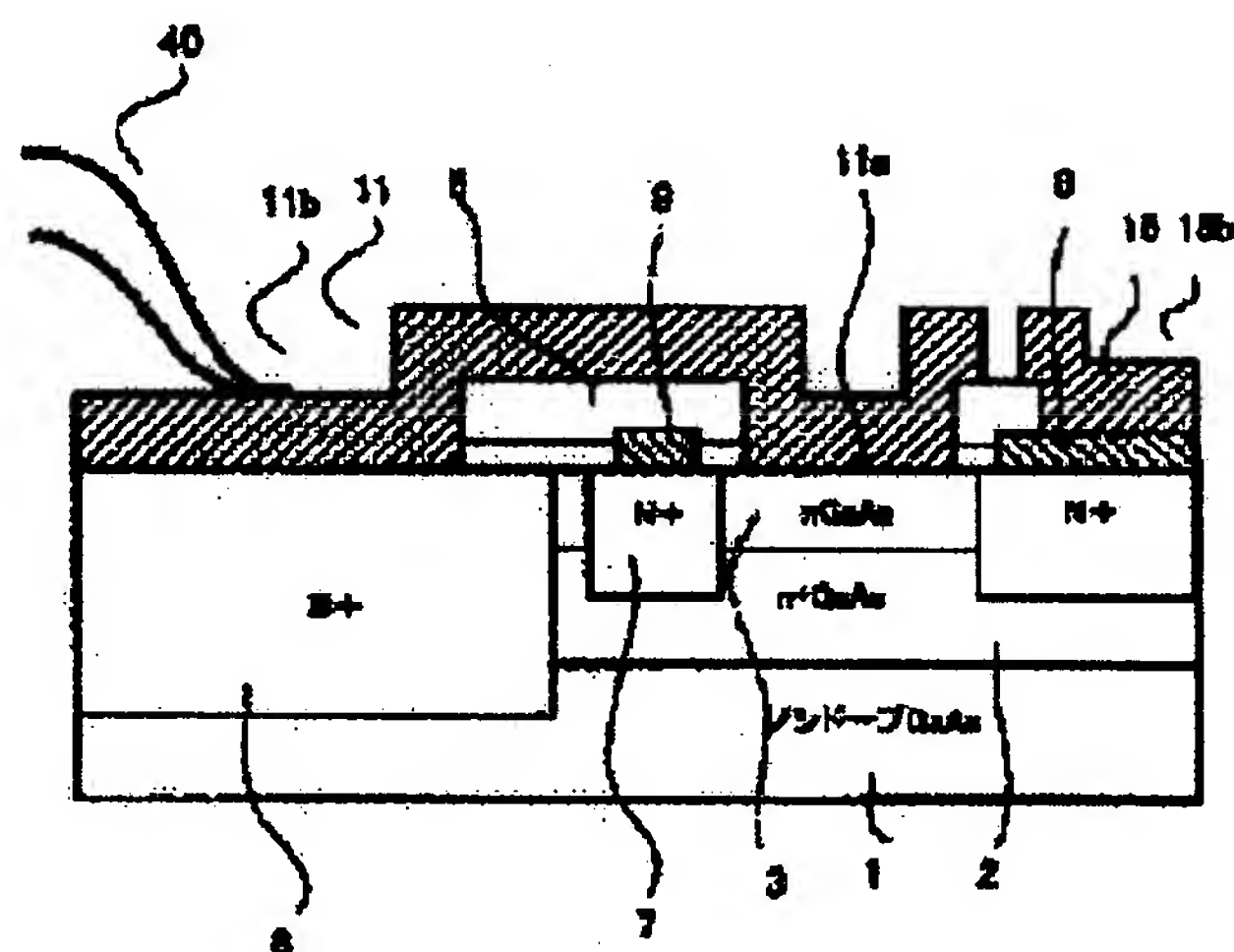
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Abstract of JP2003101036

PROBLEM TO BE SOLVED: To solve the problem in the conventional art where a polyimide layer is arranged below a bonding pad, in order to prevent generation of fracture, and the bonding pad is formed by using gold plating.

SOLUTION: An insulated region is arranged below an anode bonding pad, so that the anode bonding pad can be fixed directly on a substrate. Parasitic capacitance below the bonding pad is almost eliminated, and further, a nitride film can be used as an interlayer insulating film, so that the cost is reduced. Moreover, the manufacturing flow is simplified, and fracture and peeling due to stress at bonding are eliminated.



1 p-GaAs
 2 n-GaAs
 3 n-GaAs
 4 酸化膜
 5 絶縁膜
 7 高抵抗層形成領域

8 金めっき層
 11a 金めっき層
 11 7μm層
 11b フォトリソグラフィ
 15 金めっき層
 15a フォトリソグラフィ
 40 フォトリソグラフィ